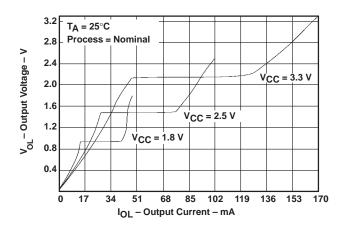
SN74AVC126 QUADRUPLE BUS BUFFER GATE WITH 3-STATE OUTPUTS

SCES255B - APRIL 1999 - REVISED DECEMBER 1999

- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- DOC™ (Dynamic Output Control) Circuit Dynamically Changes Output Impedance, Resulting in Noise Reduction Without Speed Degradation
- Dynamic Drive Capability Is Equivalent to Standard Outputs With I_{OH} and I_{OL} of ±24 mA at 2.5-V V_{CC}
- Overvoltage-Tolerant Inputs/Outputs Allow Mixed-Voltage-Mode Data Communications
- I_{off} Supports Partial-Power-Down Mode Operation
- Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages

description

A Dynamic Output Control (DOC) circuit is implemented, which, during the transition, initially lowers the output impedance to effectively drive the load and, subsequently, raises the impedance to reduce noise. Figure 1 shows typical V_{OL} vs I_{OL} and V_{OH} vs I_{OH} curves to illustrate the output impedance and drive capability of the circuit. At the beginning of the signal transition, the DOC circuit provides a maximum dynamic drive that is equivalent to a high-drive standard-output device. For more information, refer to the TI application reports, *AVC Logic Family Technology and Applications*, literature number SCEA006, and *Dynamic Output Control (DOC*TM) *Circuitry Technology and Applications*, literature number SCEA009.



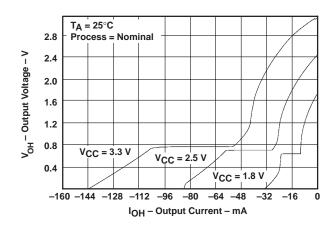


Figure 1. Output Voltage vs Output Current

This quadruple bus buffer gate is operational at 1.2-V to 3.6-V V_{CC} , but is designed specifically for 1.65-V to 3.6-V V_{CC} operation.

The SN74AVC126 features independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (OE) input is low.

To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The SN74AVC126 is characterized for operation from -40°C to 85°C.



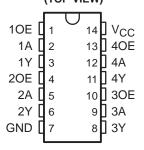
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terminal assignments

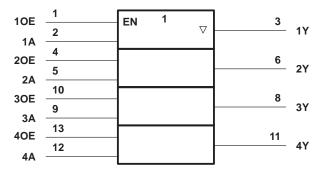
D, DGV, OR PW PACKAGE (TOP VIEW)



FUNCTION TABLE (each buffer)

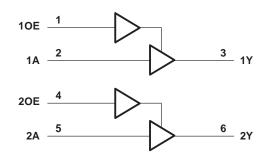
INP	JTS	OUTPUT			
OE	Α	Υ			
Н	Н	Н			
Н	L	L			
L	X	Z			

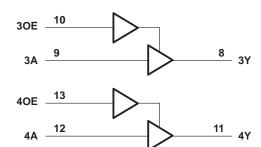
logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)







SN74AVC126 QUADRUPLE BUS BUFFER GATE WITH 3-STATE OUTPUTS SCES255B – APRIL 1999 – REVISED DECEMBER 1999

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range, V _{CC}	
Input voltage range, V _I (see Note 1)	–0.5 V to 4.6 V
Voltage range applied to any output in the high-impedance or power-off state, VO	
(see Note 1)	0.5 V to 4.6 V
Voltage range applied to any output in the high or low state, VO	
(see Notes 1 and 2)	\dots -0.5 V to V _{CC} + 0.5 V
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, IO	
Continuous current through each V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): D package	86°C/W
DGV package	127°C/W
PW package	113°C/W
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The output positive-voltage rating may be exceeded up to 4.6 V maximum if the output current rating is observed.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.



SN74AVC126 QUADRUPLE BUS BUFFER GATE WITH 3-STATE OUTPUTS

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recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
VCC	Cumply voltage	Operating	1.4	3.6	V	
	Supply voltage	Data retention only	1.2		V	
		V _{CC} = 1.2 V	VCC			
	High-level input voltage	$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	0.65 × V _{CC}			
\vee_{IH}		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V _{CC}		V	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7			
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	2			
		V _{CC} = 1.2 V		GND		
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		0.35 × V _{CC}		
VIL	Low-level input voltage	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$	V	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7		
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		0.8		
VI	Input voltage		0	3.6	V	
V	Output voltage	Active state	0	VCC	V	
VO	Output voltage	3-state	0	3.6	V	
		V _{CC} = 1.4 V to 1.6 V		-2		
laura	Static high-level output current [†]	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-4	mA	
IOHS	Static riigh-level output current	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-8		
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		-12		
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2		
lava	Static low-level output current†	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		4	mA	
IOLS	Static low-level output current	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		8		
		V _{CC} = 3 V to 3.6 V		12		
Δt/Δν	Input transition rise or fall rate	V _{CC} = 1.4 V to 3.6 V		5	ns/V	
TA	Operating free-air temperature		-40	85	°C	

T Dynamic drive capability is equivalent to standard outputs with I_{OH} and I_{OL} of ±24 mA at 2.5-V V_{CC}. See Figure 1 for V_{OL} vs I_{OL} and V_{OH} vs I_{OH} characteristics. Refer to the TI application reports, *AVC Logic Family Technology and Applications*, literature number **SCEA006**, and *Dynamic Output Control (DOC™) Circuitry Technology and Applications*, literature number **SCEA009**.

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST	CONDITIONS	VCC	MIN	TYP†	MAX	UNIT	
		I _{OHS} = -100 μA	I _{OHS} = -100 μA		V _{CC} -0.	.2			
		$I_{OHS} = -2 \text{ mA},$	V _{IH} = 0.91 V	1.4 V	1.05				
Voн		$I_{OHS} = -4 \text{ mA},$	V _{IH} = 1.07 V	1.65 V	1.2			V	
		$I_{OHS} = -8 \text{ mA},$	V _{IH} = 1.7 V	2.3 V	1.75				
		$I_{OHS} = -12 \text{ mA},$	V _{IH} = 2 V	3 V	2.3				
		I _{OLS} = 100 μA		1.4 V to 3.6 V			0.2		
		$I_{OLS} = 2 \text{ mA},$	$V_{IL} = 0.49 \ V$	1.4 V			0.4	V	
VOL		$I_{OLS} = 4 \text{ mA},$	$V_{IL} = 0.57 V$	1.65 V			0.45		
		$I_{OLS} = 8 \text{ mA},$	$V_{IL} = 0.7 V$	2.3 V			0.55		
		$I_{OLS} = 12 \text{ mA},$	$V_{IL} = 0.8 V$	3 V			0.7		
Ц	Control inputs	$V_I = V_{CC}$ or GND		3.6 V			±2.5	μΑ	
l _{off}		V_I or $V_O = 3.6 V$		0			±10	μΑ	
loz		$V_O = V_{CC}$ or GND		3.6 V			±12.5	μΑ	
Icc		$V_I = V_{CC}$ or GND,	IO = 0	3.6 V			40	μΑ	
	Control inputs			2.5 V					
] _{C.}		V. – V. – or CND	V. – V. a or CND]	
Ci	Data inputs	$V_I = V_{CC}$ or GND		2.5 V				pF	
				3.3 V					
	Outputo	Vo – Voo or CND		2.5 V					
Co	Outputs	AO = ACC OLGIND	VO = VCC or GND					pF	

[†] Typical values are measured at $T_A = 25$ °C.

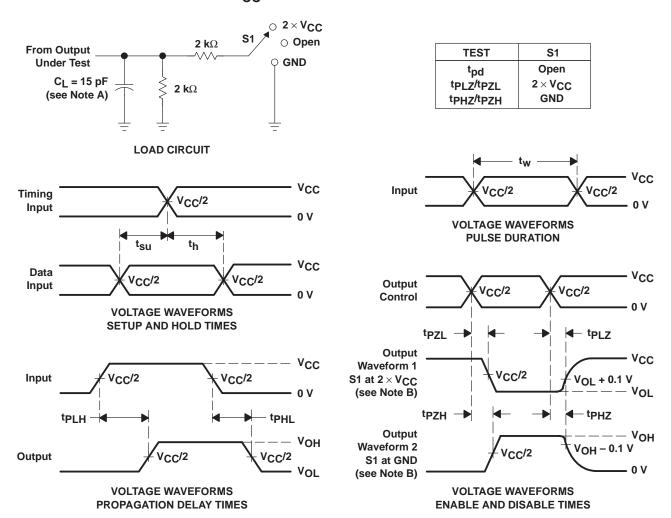
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 through 5)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.2 V	V _{CC} =	1.5 V 1 V	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
			TYP	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
tpd	Α	Y										ns
t _{en}	OE	Υ										ns
t _{dis}	OE	Y										ns

operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	UNIT	
	TANAMETER	1201 GONDITIONS	TYP	TYP	TYP	ONIT	
C _{pd}	Power dissipation capacitance per buffer	$C_L = 0$, $f = 10 \text{ MHz}$				pF	

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.2 \text{ V}$ AND 1.5 V \pm 0.1 V



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq 2$ ns. $t_f \leq 2$ ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLz and tpHz are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms



S1

Open

2×V_{CC}

GND

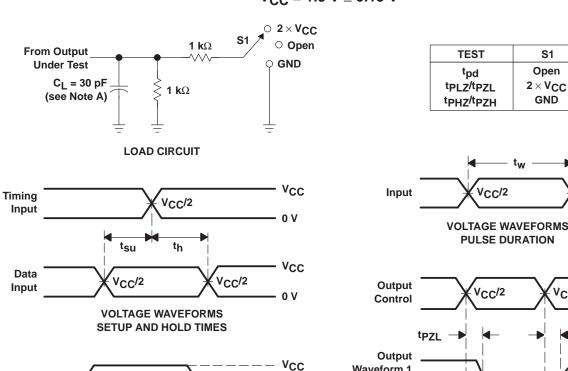
PRODUCT PREVIEW

VCC

0 V

V_{CC}/2

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$



V_{CC}/2

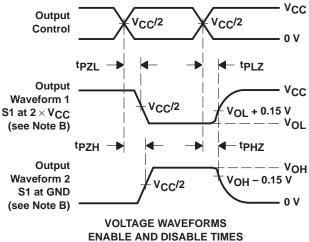
0 V

Vон

 v_{OL}

^tPHL

 $V_{CC}/2$



V_{CC}/2

NOTES: A. C_I includes probe and jig capacitance.

V_{CC}/2

Input

Output

^tPLH

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$, $t_f \leq 2 \ ns$, $t_f \leq 2 \ ns$.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpHZ are the same as tdis.

V_{CC}/2

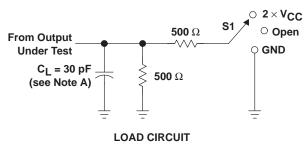
VOLTAGE WAVEFORMS

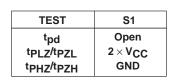
PROPAGATION DELAY TIMES

- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$





V_{CC}/2

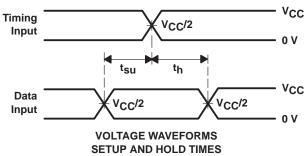
VOLTAGE WAVEFORMS PULSE DURATION

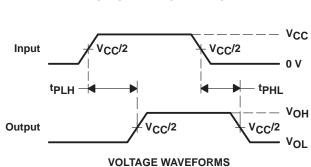
Input

VCC

0 V

V_{CC}/2





PROPAGATION DELAY TIMES

VCC Output V_{CC}/2 V_{CC}/2 Control 0 V tp7I - tpi 7 Output VCC Waveform 1 V_{CC}/2 S1 at $2 \times V_{CC}$ V_{OL} + 0.15 V (see Note B) - V_{OL} - tPHZ ^tPZH Output - Vон Waveform 2 V_{OH} – 0.15 V S1 at GND 0 V (see Note B) **VOLTAGE WAVEFORMS**

ENABLE AND DISABLE TIMES

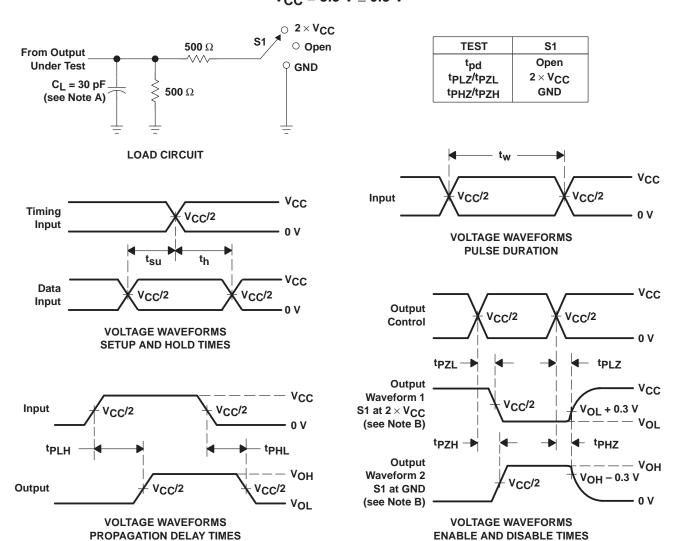
NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 4. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION V_{CC} = 3.3 V \pm 0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq 2$ ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as tdis.
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. tpLH and tpHL are the same as tpd.

Figure 5. Load Circuit and Voltage Waveforms



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